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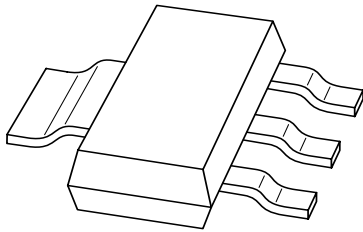
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Kind regards,

Team Nexperia

DATA SHEET



BF723

PNP high-voltage transistor

Product data sheet
Supersedes data of 1996 Dec 05

1999 Apr 21

PNP high-voltage transistor

BF723

FEATURES

- Low feedback capacitance.

APPLICATIONS

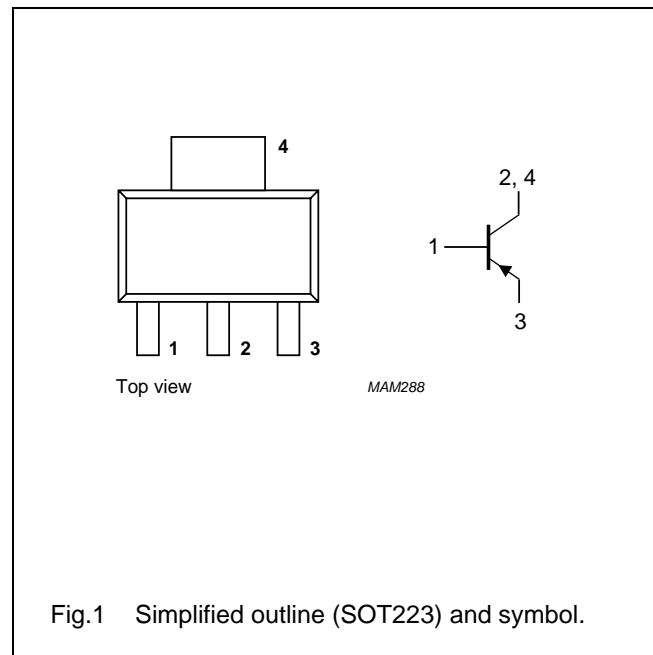
- Class-B video output stages of colour television receivers
- General purpose high voltage circuits.

DESCRIPTION

PNP transistor in a SOT223 plastic package.
NPN complement: BF722.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–250	V
V_{CEO}	collector-emitter voltage	open base	–	–250	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1	–	1.2	W
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

Note

1. Device mounted on printed-circuit board, single sided copper, tinned, mounting pad for collector 1 cm². For other mounting conditions, see “Thermal considerations for SOT223 in the General Part of associated Handbook”.

PNP high-voltage transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	106	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point	note 1	25	K/W

Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -200\text{ V}$	–	–10	nA
		$I_E = 0; V_{CB} = -200\text{ V}; T_j = 150\text{ °C}$	–	–10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$I_C = -25\text{ mA}; V_{CE} = -20\text{ V}$	–50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -30\text{ mA}; I_B = -5\text{ mA}$	–	–0.6	V
C_{re}	feedback capacitance	$I_C = i_c = 0; V_{CE} = -30\text{ V}; f = 1\text{ MHz}$	–	2.5	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	60	–	MHz

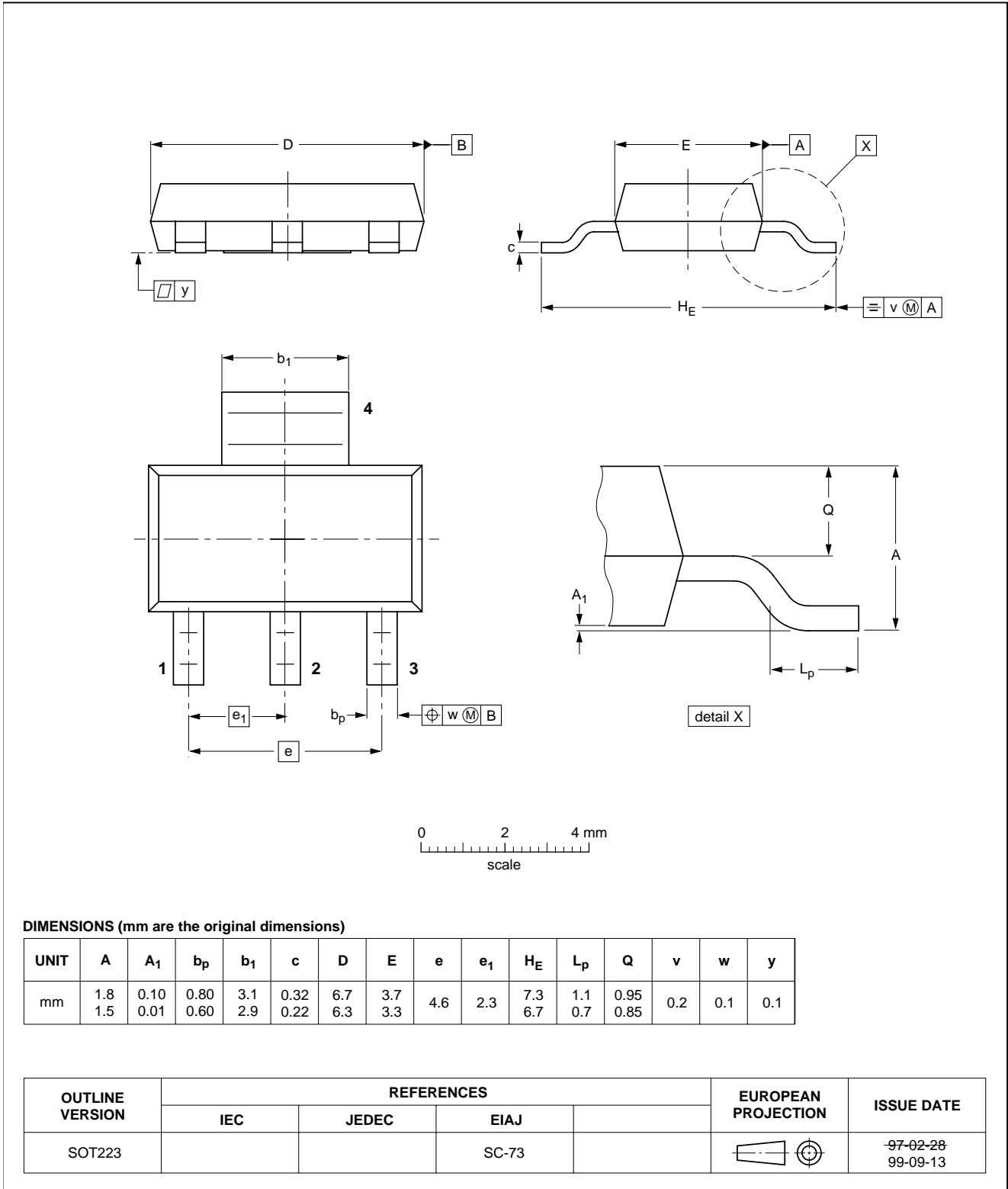
PNP high-voltage transistor

BF723

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



PNP high-voltage transistor

BF723

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

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